## I-V CHARACTEISTICS CURVE

PRESENTED BY
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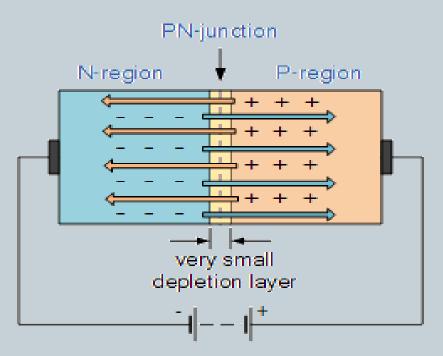
#### **OPERATING REGION & BIASING**



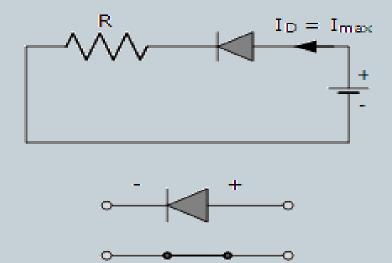
- 1. Zero Bias No external voltage potential is applied to the PN junction diode.
- 2. Reverse Bias The voltage potential is connected negative, (-ve) to the P-type material and positive, (+ve) to the N-type material across the diode which has the effect of **Increasing** the PN junction diode's width.
- 3. Forward Bias The voltage potential is connected positive, (+ve) to the P-type material and negative, (-ve) to the N-type material across the diode which has the effect of **Decreasing** the PN junction diodes width.

- When a diode is **Zero Biased** no external energy source is applied and a natural **Potential Barrier** is developed across a depletion layer which is approximately 0.5 to 0.7v for silicon diodes and approximately 0.3 of a volt for germanium diodes.
- When a junction diode is Forward Biased the thickness of the depletion region reduces and the diode acts like a short circuit allowing full circuit current to flow.
- When a junction diode is **Reverse Biased** the thickness of the depletion region increases and the diode acts like an open circuit blocking any current flow, (only a very small leakage current will flow).

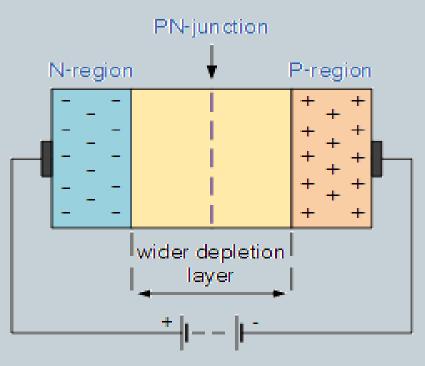
#### FORWARD BIASING

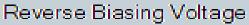


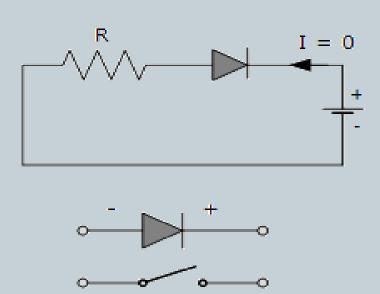
Forward Biasing Voltage



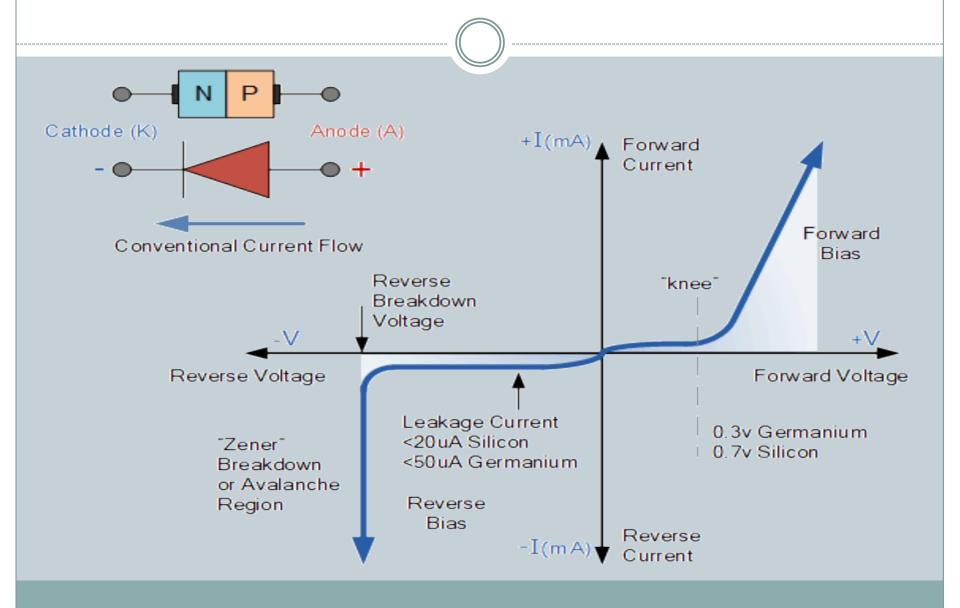
### **REVERSE BIASING**







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In the next class....

- > Advantages and disadvantages of pn junction diode
- > Applications

# THANK YOU